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AMENDMENTS TO THE SPECIFICATION**OFFICE OF PETITIONS**

Change the title to read:

METHOD OF MANUFACTURING SEMICONDUCTOR HAVING GROUP
II – GROUP VI COMPOUNDS DOPED WITH NITROGEN

Change the paragraph beginning at page 5, line 16, as follows:

The first of two primary semiconductor layers is n-type semiconductor layer 18. In a preferred embodiment of the invention this n-type semiconductor is cadmium sulfide (CdS). The next major semiconductor layer is a p-type semiconductor 20, which is preferably cadmium telluride (CdTe). Numerous other semiconductor layers can be used for these two primary semiconductors. It is to be understood that an intrinsic semiconductor layer, not shown, can be disposed between the p-type semiconductor layer and the n-type semiconductor layer in conjunction with the present invention. A layer of back contact material is indicated at 22. The back contact layer 22 acts to provide an interface with conductive layer 24, which is the second of the two ohmic contacts or electrodes for the photovoltaic cell 10. The conductive layer 24 contains a conductive lead 26 for conducting current through the electric circuit, not shown. Typically, the conductive electrode layer is made of nickel, titanium, chromium, aluminum, or some other conductive material. An additional protective or buffer layer of zinc telluride, not shown, can be positioned between the back contact layer 22 and the cadmium telluride semiconductor layer 20 to protect the cadmium telluride layer from foreign contamination by migration, but such a layer has been found to be unnecessary in the present embodiment.

Change the paragraph beginning at page 7, line 7, as follows:

Ord While the semiconductor of ~~if~~ the invention is very useful when incorporated in a photovoltaic cell, there are other uses for the nitrogen doped group II-group VI compounds. For example, the semiconductor of the invention can be used in combination with a large-area flat panel light emitting display, wherein the nitrogen-doped group II-group VI compound forms a p-type heavily doped layer of a light emitting diode.